

Please amend the subject application as follows:

**IN THE CLAIMS**

Please cancel claims 18-25 without prejudice and accept an amended claims 1 and 15 and new claims 26-27 as follows:

1. (Currently amended) A method of manufacturing a thin film transistor array panel, the method comprising:

forming a gate conductor on an insulating substrate;

forming a gate insulating layer;

forming a semiconductor member;

forming a data conductor; and

forming a pixel electrode connected to the ~~drain electrode~~ data conductor,

wherein the gate conductor, the data conductor, and the pixel electrode are formed using a single etchant.

2. (Original) The method of claim 1, wherein the etchant comprises about 50-60%  $\text{H}_3\text{PO}_4$ , about 6-10%  $\text{HNO}_3$ , about 15-25%  $\text{CH}_3\text{COOH}$ , about 2-5% stabilizer, and deionized water.

3. (Original) The method of claim 2, wherein the stabilizer comprises oxy-hydride inorganic acid represented by  $\text{M}(\text{OH})_x\text{L}_y$ , where M includes at least one of Zn, Sn,

Cr, Al, Ba, Fe, Ti, Si and B, L includes at least one of H<sub>2</sub>O, NH<sub>3</sub>, CN and NH<sub>2</sub>R (where R is alkyl group), X is 2 or 3, and Y is 0, 1, 2 or 3.

4. (Original) The method of claim 3, wherein the gate conductor comprises a lower film of Al or Al alloy and an upper film of Mo or Mo alloy.

5. (Original) The method of claim 4, wherein the lower film and the upper film comprises Al--Nd and MoW, respectively.

6. (Original) The method of claim 4, wherein the data conductor comprises Mo or Mo alloy.

7. (Original) The method of claim 6, wherein the pixel electrode comprises IZO.

8. (Original) The method of claim 7, wherein the lower layer of the gate conductor, the upper layer of the gate conductor, the data conductor, and the pixel electrode have thickness of about 1,500-3,000 Å, about 300-600 Å, about 1,500-3,000 Å, and about 800-1,000 Å, respectively.

9. (Original) The method of claim 1, wherein the etchant comprises about 65-75% H<sub>3</sub>PO<sub>4</sub>, about 0.5-4% HNO<sub>3</sub>, about 9-13% CH<sub>3</sub>COOH, about 2-5% stabilizer,

and deionized water.

10. (Original) The method of claim 9, wherein the stabilizer comprises oxy-hydride inorganic acid represented by  $M(OH)_xL_Y$ , where M includes at least one of Zn, Sn, Cr, Al, Ba, Fe, Ti, Si and B, L includes at least one of  $H_2O$ ,  $NH_3$ , CN and  $NH_2R$  (where R is alkyl group), X is 2 or 3, and Y is 0, 1, 2 or 3.

11. (Original) The method of claim 10, wherein the gate conductor comprises a lower film of Al or Al alloy and an upper film of Mo.

12. (Original) The method of claim 11, wherein the lower film comprises Al--Nd.

13. (Original) The method of claim 11, wherein the data conductor comprises a bottom layer of Mo, an intermediate layer of Al or Al alloy, and a top layer of Mo.

14. (Original) The method of claim 13, wherein the pixel electrode comprises IZO.

15. (Currently amended) A method of manufacturing a thin film transistor array panel, the method comprising:

forming a gate conductor on an insulating substrate;

forming a gate insulating layer;

forming a semiconductor member;

forming a data conductor; and

forming a pixel electrode connected to the ~~drain electrode~~ data conductor,

wherein at least one of the gate conductor, the data conductor, and the pixel electrode are formed by using an etchant including a phosphoric acid of about 50-60%, a nitric acid of about 6-10%, an acetic acid of about 15-25%, a stabilizer of about 2-5% stabilizer, and deionizer water, or an etchant including a phosphoric acid of about 65-75%, a nitric acid of about 0.5-4%, an acetic acid of about 9-13%, a stabilizer of about 2-5% stabilizer, and deionizer water,

wherein the stabilizer includes oxy-hydride inorganic acid represented by  $M(OH)_X L_Y$ , where M includes at least one of Zn, Sn, Cr, Al, Ba, Fe, Ti, Si and B, L includes at least one of  $H_2O$ ,  $NH_3$ , CN and  $NH_2R$  (where R is alkyl group), X is 2 or 3, and Y is 0, 1, 2, or 3.

16. (Original) The method of claim 15, wherein at least two of the gate conductor, the data conductor, and the pixel electrode comprise at least one of Mo, Mo alloy, Al, Al alloy, and IZO.

17. (Original) The method of claim 15, wherein each of the gate conductor, the data conductor, and the pixel electrode comprises at least one of Mo, Mo alloy, Al, Al alloy, and IZO.

18. – 25. (canceled)

26. (New) The method of claim 1, wherein at least one of the gate conductor and the data conductor comprises at least two layers.

27. (New) A method of manufacturing a thin film transistor array panel, the method comprising:

- forming a gate conductor on an insulating substrate;

- forming a gate insulating layer;

- forming a semiconductor member;

- forming a data conductor; and

- forming a pixel electrode connected to the data conductor,

- wherein the gate conductor, the data conductor, and the pixel electrode are formed using a single etchant,

- wherein the single etchant includes at least one of a phosphoric acid, a nitric acid, and an acetic acid.